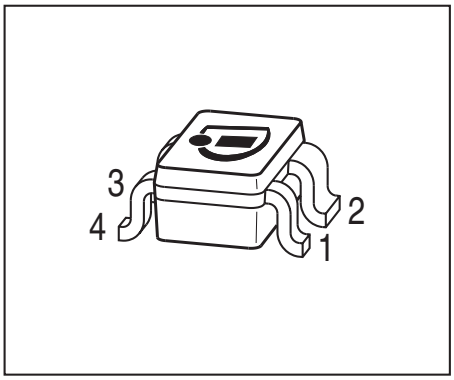
NPN Silicon RF Transistor*



- For low voltage / low current applications
- Ideal for ESD protected low noise amplification
- Low noise figure: 1.1 dB at 1.8 GHz
- Excellent ESD performance
  typical value 1500V (HBM)
- High f_T of 22 GHz
- Pb-free (RoHS compliant) package [1)]
- Qualified according AEC Q101

* Short term description

ESD (**E**lectro**s**tatic **d**ischarge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP460	ABs	1 = E	2 = C	3 = E	4=B	-	-	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
T_A > 0 °C		4.5	
T_A ≤ 0 °C		4.2	
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	50	mA
Base current	I_B	5	
Total power dissipation[2)] T_S ≤ 100°C	P_{tot}	200	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

[1]Pb-containing package may be available upon special request
[2]T_S is measured on the collector lead at the soldering point to the pcb

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Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 250	K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	4.5	5.8	-	V
Collector-emitter cutoff current V_{CE} = 15 V, V_{BE} = 0	I_{CES}	-	-	10	µA
Collector-base cutoff current V_{CB} = 5 V, I_E = 0	I_{CBO}	-	-	100	nA
Emitter-base cutoff current V_{EB} = 0,5 V, I_C = 0	I_{EBO}	-	-	1	µA
DC current gain I_C = 20 mA, V_{CE} = 3 V, pulse measured	h_{FE}	90	120	160	-

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency I_C = 30 mA, V_{CE} = 3 V, f = 1 GHz	f_T	16	22	-	GHz
Collector-base capacitance V_{CB} = 3 V, f = 1 MHz, V_{BE} = 0 , emitter grounded	C_{cb}	-	0.32	0.45	pF
Collector emitter capacitance V_{CE} = 3 V, f = 1 MHz, V_{BE} = 0 , base grounded	C_{ce}	-	0.28	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz, V_{CB} = 0 , collector grounded	C_{eb}	-	0.55	-	
Noise figure I_C = 5 mA, V_{CE} = 3 V, Z_S = Z_{Sopt} , f = 1.8 GHz f = 3 GHz	F	 - -	 1.1 1.35	 - -	dB
Power gain, maximum stable[1)] I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 1.8 GHz	G_{ms}	-	17.5	-	dB
Power gain, maximum available[1)] I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt} , f = 3 GHz	G_{ma}	-	12.5	-	dB
Transducer gain I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_L = 50Ω, f = 1,8 GHz f = 3 GHz	$\lvert S_{21e}\rvert^2$	 - -	 15 10.5	 - -	dB
Third order intercept point at output[2)] V_{CE} = 3 V, I_C = 20 mA, f = 1.8 GHz	IP_3	-	27.5	-	dBm
1dB Compression point at output I_C = 20 mA, V_{CE} = 3 V, f = 1.8 GHz	P_{-1dB}	-	11.5	-	

[1] $G_{ma} = \lvert S_{21} / S_{12} \rvert (k-(k^2-1)^{1/2})$, $G_{ms} = \lvert S_{21} / S_{12} \rvert$

[2] IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

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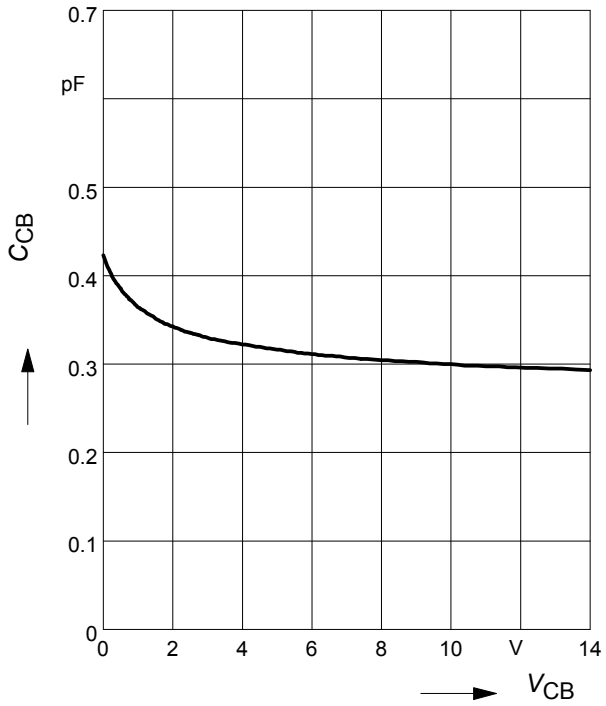
Collector-base capacitance $C_{cb}= f(V_{CB})$

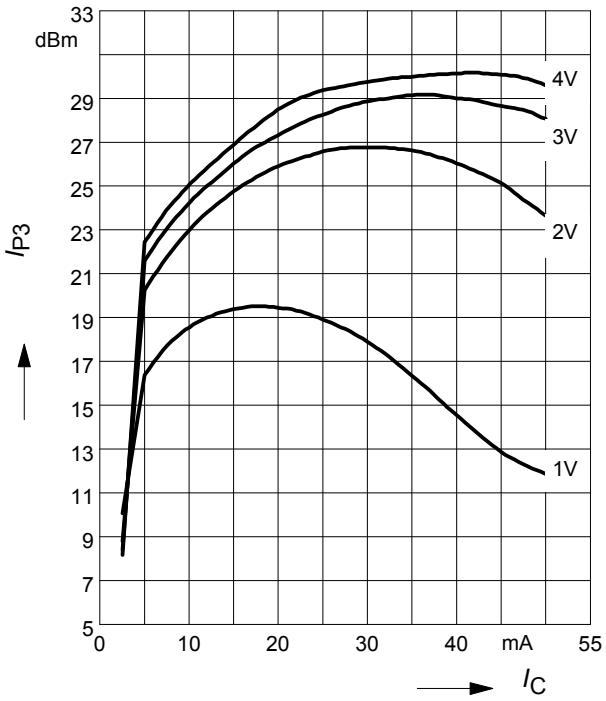
f = 1MHz



Third order Intercept Point $IP_3=f(I_C)$

(Output, $Z_S=Z_L=50\Omega$)

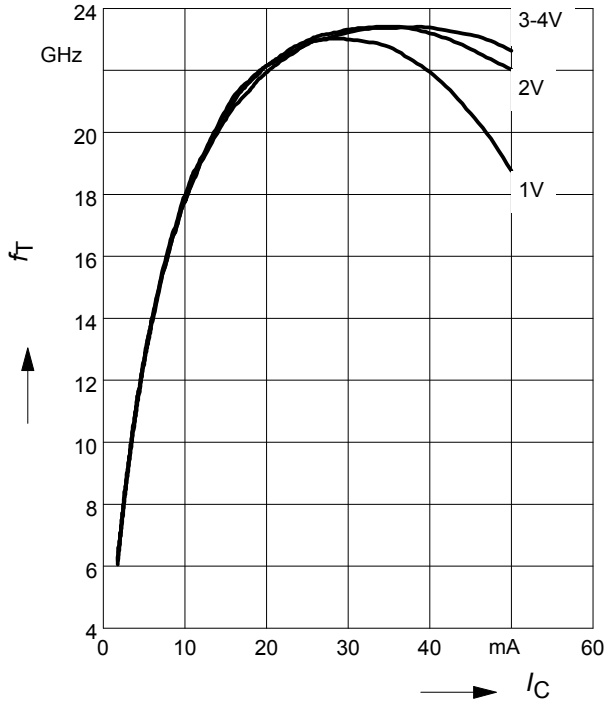
V_{CE} = parameter, f = 1800MHz -



Transition frequency $f_T= f(I_C)$

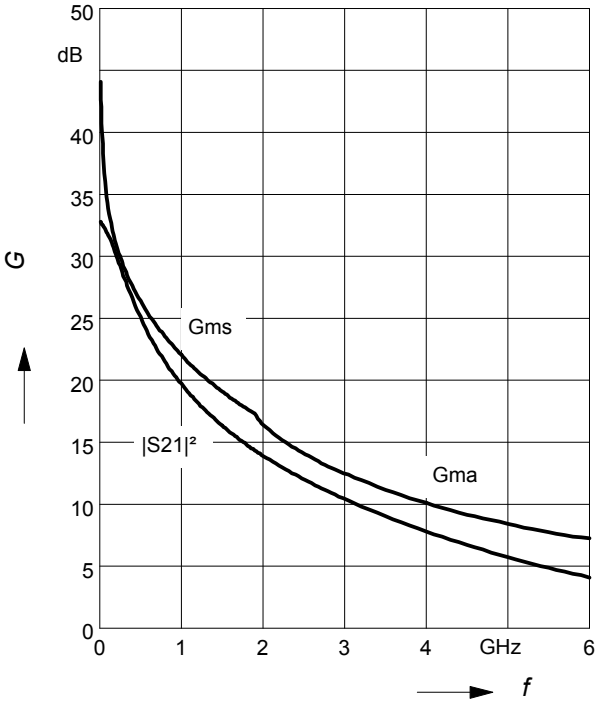
f = 1 GHz

V_{CE} = parameter in V



Power gain G_{ma}, G_{ms}, $|S_{21}|^2 = f(f)$

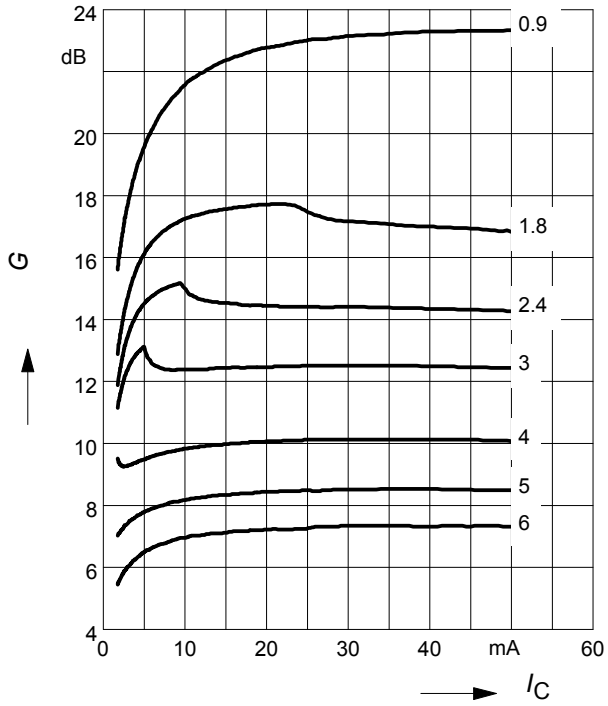
V_{CE} = 3 V, I_C = 20 mA



Power gain G_{ma}, G_{ms} = f (I_C)

V_{CE} = 3V

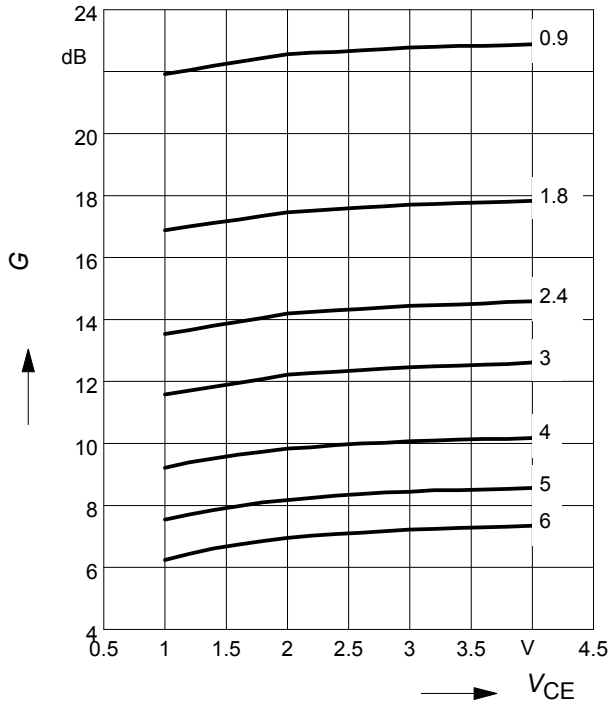
f = parameter in GHz



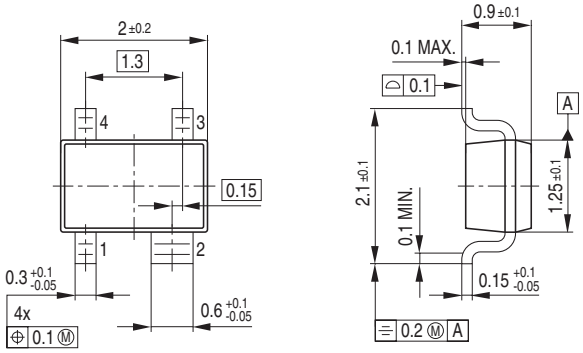
Power gain G_{ma}, G_{ms} = f (V_{CE})

I_C = 20 mA

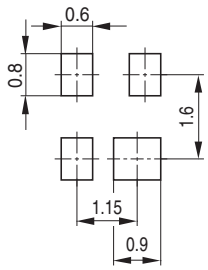
f = parameter in GHz



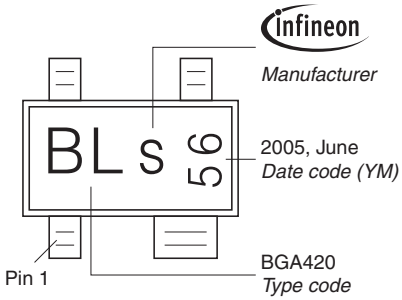
Package Outline



Foot Print

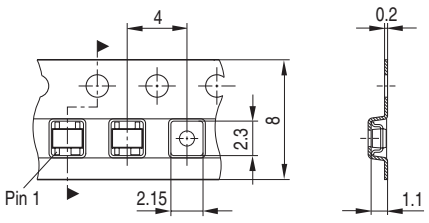


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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